

FORM PTO-1449 (Rev. 2-32)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		SERIAL NO. NOT YET ASSIGNED		DOCKET NO. Q54431	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				APPLICANT Toshiro HAYAKAWA, Toshiaki FUKUNAGA and Mitsugu WADA			
				FILING DATE May 20, 1999			GROUP 2851
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>J3</i>		4,567,060	01/28/86	HAYAKAWA et al	427	87	
<i>(Handwritten diagonal lines across the table)</i>							
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO	
<i>(Handwritten diagonal lines across the table)</i>							
OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)							
<i>J3</i>		S. O'Brien et al, High power wide aperture AlGaAs-based lasers at 870nm, January 22, 1998, Vol.34, No.2, page 184 - 186					
<i>J3</i>		T. Fukunaga et al, Highly Reliable Operation of High-Power In GaAsP/InGaP/AlGaAs 0.8 μ m Separate Confinement Heterostructure Lasers, September 15, 1995, Vol. 34, No.9B, p.L1175 -L117					
<i>J3</i>		J.K. Wade et al, 6.1 W continuous wave front-facet power from Al-free active-region (λ = 805 nm) diode lasers, January 5, 1998, Vol., 72, No.1, p.4 - 6					
<i>J3</i>		M.A. Emanuel et al, High-Power Laser Diodes at Various Wavelengths, 1997, Vol. 3001, p.2 - 6					
<i>J3</i>		Low-threshold room-temperature cw operation of $(AlGaAs)_m(GaAs)_n$ superlattice quantum well lasers emitting at ~ 680nm, September 7, 1987, Vol.51, p.707 - 709					
<i>(Handwritten diagonal lines across the table)</i>							

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application. (Form PTO-1449 [8-4])

Form PTO-1449 (Rev. 2-32)		U.S. Department of Commerce Patent & Trademark Office		Atty. Docket No. Q54431	Serial No. 09/315,068		
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant: Toshiro HAYAKAWA, et al.					
		Filing Date: May 20, 1999	Group: 2874 2881	JAN 04 2001 U.S. PATENT & TRADEMARK OFFICE OIPC			
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date (if appropriate)
13.		4,728,628	3/1/88	Fiddyment et al.	437	225	
FOREIGN PATENT DOCUMENTS							
	Document	Date	Country	Class	Sub-class	Translation Yes/No	
13.	7-74425	3/17/95	Japan	H01S	3/18		
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
13	Milind R. Gokhale, et al.; "High-Power High-Efficiency 0.98- μ m Wavelength InGaAs-(In)GaAs(P)-InGaP Broadened Waveguide Lasers Grown by Gas-Source Molecular Beam Epitaxy" vol. 33; No. 12; December 1997; pages 2266-2276						
13	Electronics Letters; vol. 28; No. 16; pages 1531-1532; July 1992						
EXAMINER: JEFFREY RATH		DATE CONSIDERED: 2/7/2001					

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			Q54431	09/315,068	
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U.S. PATENT DOCUMENTS					
Examiner Initial		Document Number	Name	Class	Sub-Class
TRADEMARK					
(if appropriate)					
FOREIGN PATENT DOCUMENTS					
	Document	Date	Country	Class	Sub-class
Translation Yes/No					
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
Wade J K et al; "6.1 W CONTINUOUS WAVE FRONT-FACET POWER FROM AL-FREE ACTIVE-REGION (LAMBDA=805 NM) DIODE LASERS"; vol. 72 no. 1; 1/5/98 pages 4-6; XP000737351					
Unger P et al; "JUNCTION-SIDE UP OPERATION OF (AL) GAINP LASERS WITH VERY LOW THRESHOLD CURRENTS"; vol. 28, no. 16; 7/30/92; pages 1531-1532; XP000309705					
Erber G et al; "A STUDY OF STRUCTURES WITH A1-FREE QWs IN AlGaAs WAVEGUIDES FOR LASER DIODES EMITTING AT 800 NM" vol 1; pages 46-47; XP002148474					
Iwai N et al.; "LOW THRESHOLD CURRENT 1.3MUM INASP QW ACIS LASERS" vol. 34; no. 9; 4/30/98; pages 890-891; XP000799146					
Fukunaga T et al; "HIGHLY RELIABLE OPERATIONS OF HIGH-POWER INGAASP/INGAP/ALGAAS 0.8 MU M SEPARATE CONFINEMENT HETEROSTRUCTURE LASERS" vol 34; no. 9B; 9/15/95; XP000702502					
EXAMINER:	JEFFREY ZAHN		DATE CONSIDERED: → Feb 2001		
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